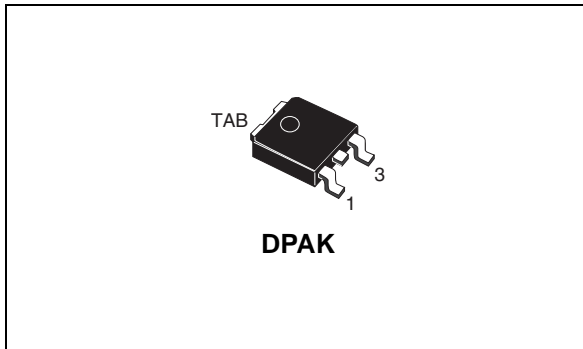
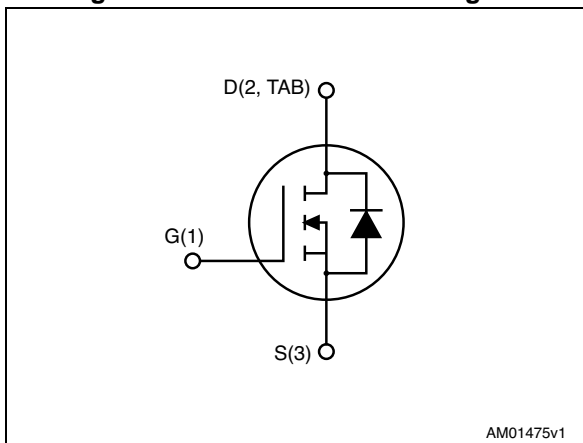


## Automotive-grade N-channel 40 V, 5.5 mΩ typ., 80 A STripFET™ VI DeepGATE™ Power MOSFET in a DPAK package

Datasheet – production data



**Figure 1. Internal schematic diagram**



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STD80N4F6	40 V	6 mΩ	80 A

- Designed for automotive applications and AEC-Q101 qualified
- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using the 6<sup>th</sup> generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R<sub>DS(on)</sub> in all packages.

**Table 1. Device summary**

Order code	Marking	Package	Packaging
STD80N4F6	80N4F6	DPAK	Tape and reel

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	56	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
$I_{AV}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_{Jmax}$ )	40	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AV}$ , $V_{DD} = 25\text{ V}$ )	149	mJ
	Derating factor	0.47	W/ $^\circ\text{C}$
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Max. operating junction temperature		$^\circ\text{C}$

1. Current limited by package.
2. Pulse width limited by safe operating area

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.14	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50	$^\circ\text{C/W}$

1. When mounted on FR-4 board of  $\text{inch}^2$ , 2 oz Cu

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu A, V_{GS} = 0$	40			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 40\text{ V}$			1	$\mu A$
		$V_{DS} = 40\text{ V}, T_C = 125\text{ °C}$			100	$\mu A$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		5.5	6	m $\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	2150	-	pF
$C_{oss}$	Output capacitance		-	335	-	pF
$C_{riss}$	Reverse transfer capacitance		-	160	-	pF
$Q_g$	Total gate charge	$V_{DD} = 20\text{ V}, I_D = 80\text{ A}, V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14</a> )	-	36	-	nC
$Q_{gs}$	Gate-source charge		-	11	-	nC
$Q_{gd}$	Gate-drain charge		-	9	-	nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}, I_D = 40\text{ A}, R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15</a> )	-	10.5	-	ns
$t_r$	Rise time		-	7.6	-	ns
$t_{d(off)}$	Turn-off delay time		-	46.1	-	ns
$t_f$	Fall time		-	11.9	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40 \text{ A}$ , $V_{GS} = 0$	-		1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 80 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 32 \text{ V}$ (see <a href="#">Figure 17</a> )	-	41.1		ns
$Q_{rr}$	Reverse recovery charge		-	43.6		nC
$I_{RRM}$	Reverse recovery current		-	2.1		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

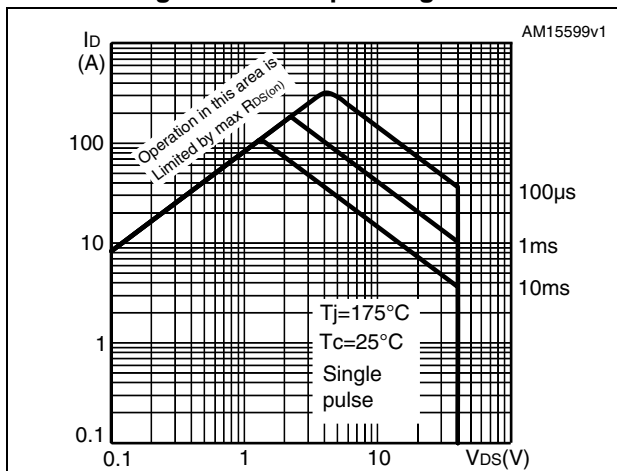


Figure 3. Thermal impedance

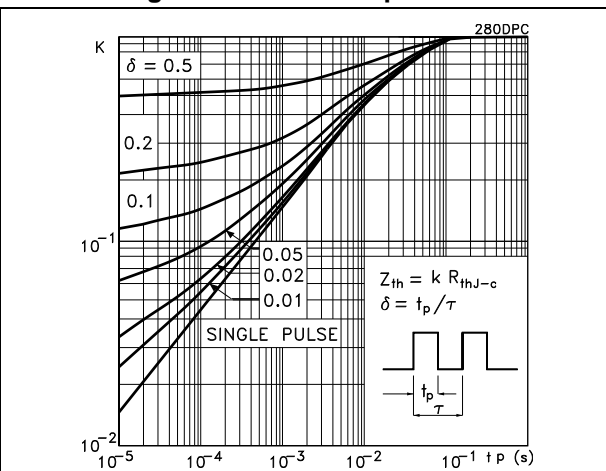


Figure 4. Output characteristics

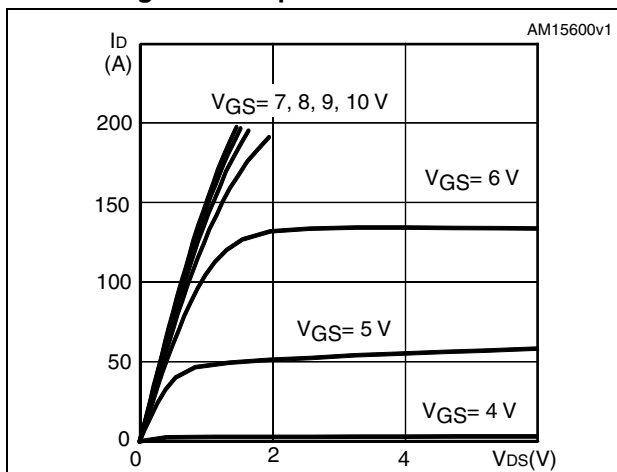


Figure 5. Transfer characteristics

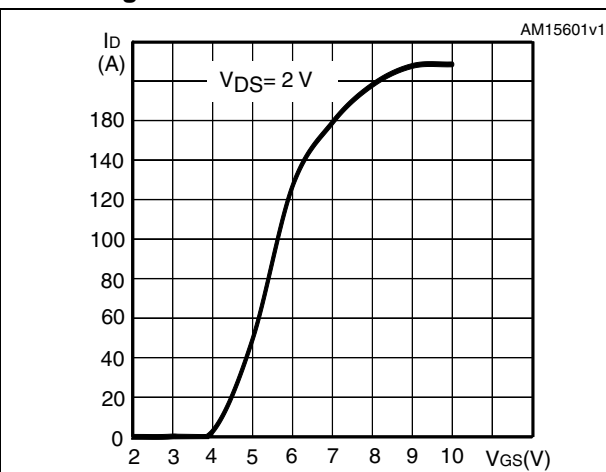


Figure 6. Gate charge vs gate-source voltage

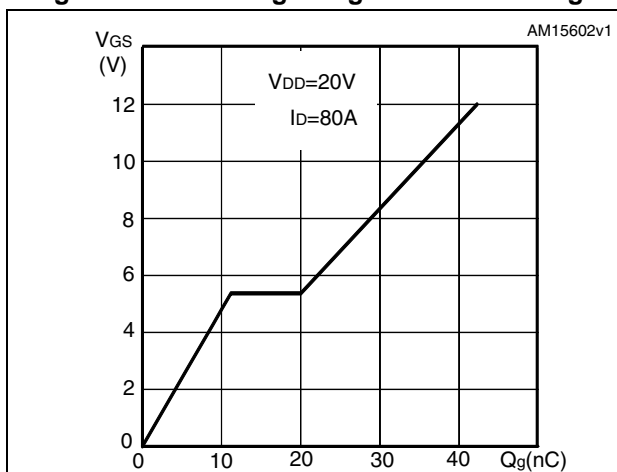


Figure 7. Static drain-source on-resistance

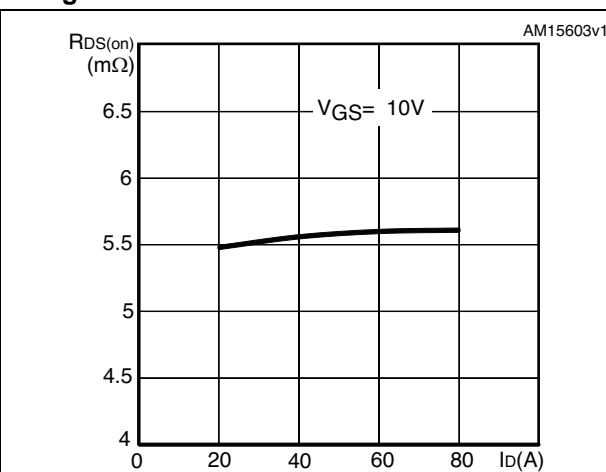


Figure 8. Capacitance variations

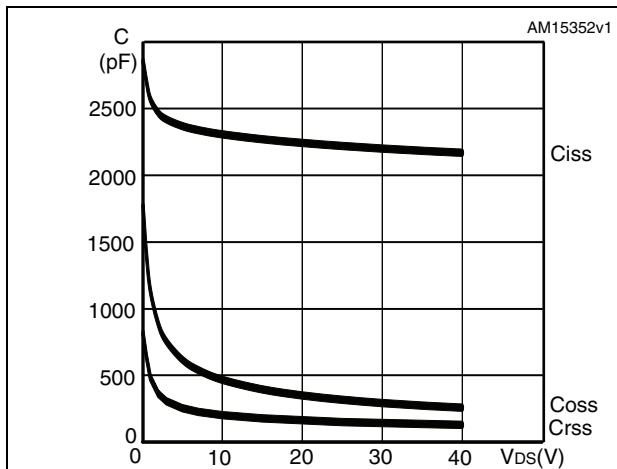


Figure 9. Drain-source diode forward characteristics

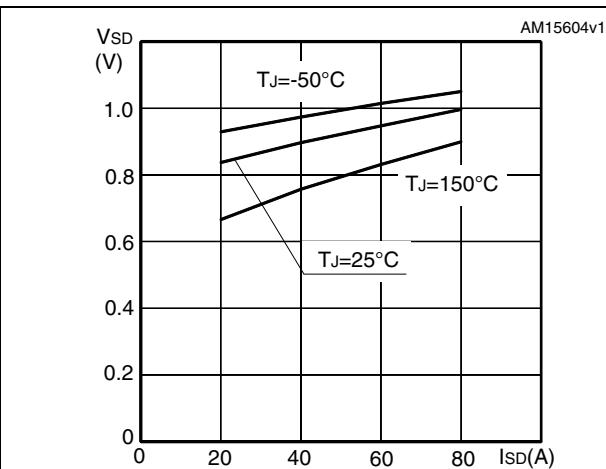


Figure 10. Normalized gate threshold voltage vs temperature

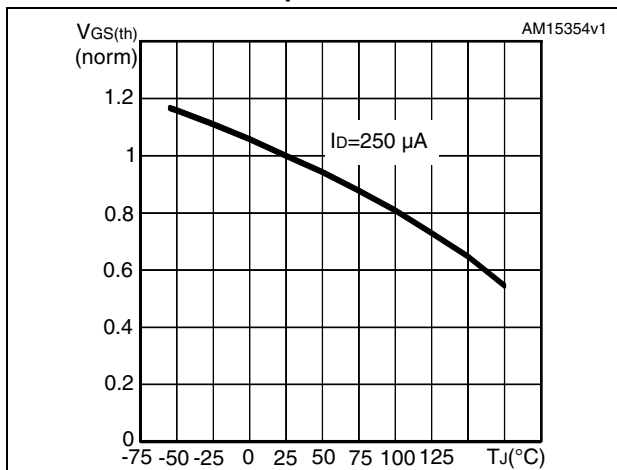


Figure 11. Normalized on-resistance vs temperature

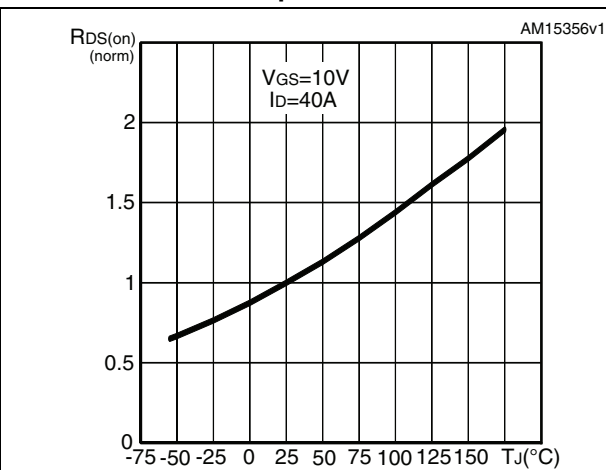
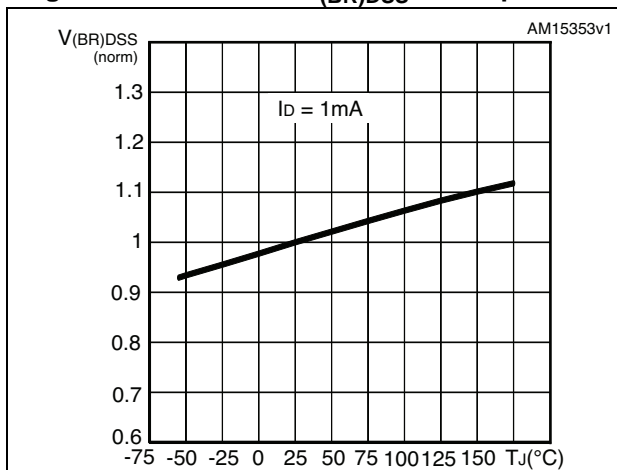


Figure 12. Normalized  $v_{(BR)DSS}$  vs temperature



### 3 Test circuits

Figure 13. Switching times test circuit for resistive load

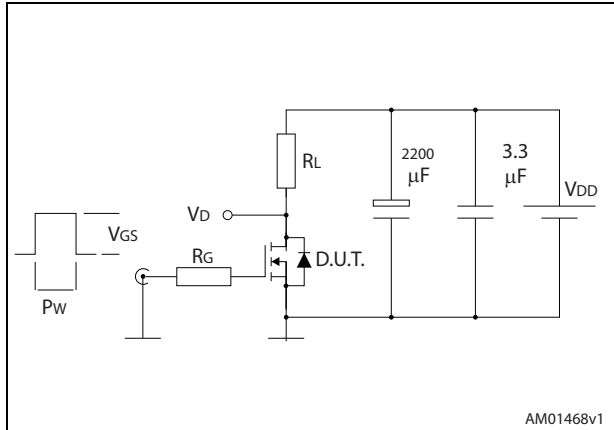


Figure 14. Gate charge test circuit

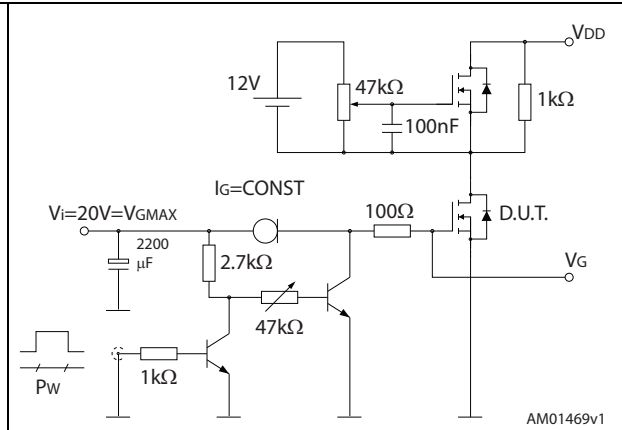


Figure 15. Test circuit for inductive load switching and diode recovery times

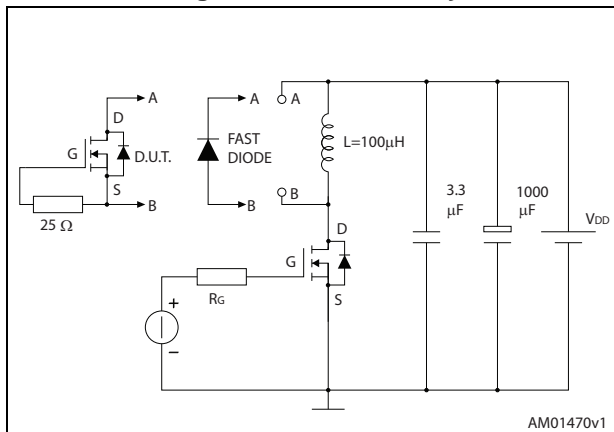


Figure 16. Unclamped inductive load test circuit

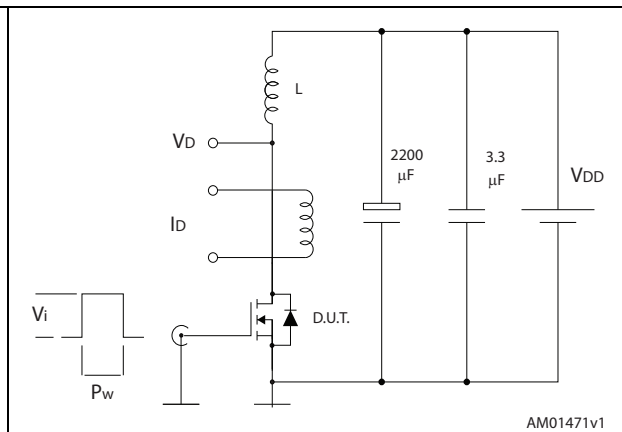


Figure 17. Unclamped inductive waveform

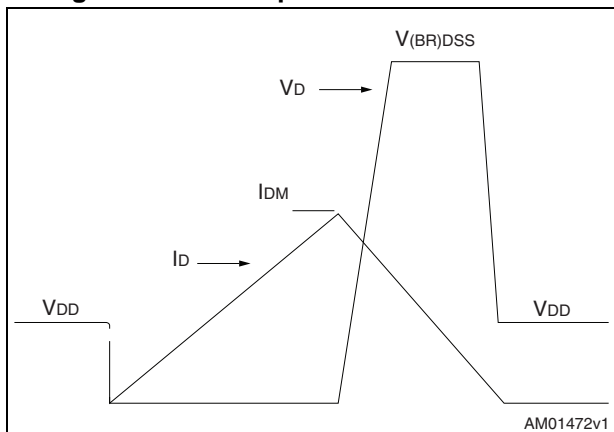
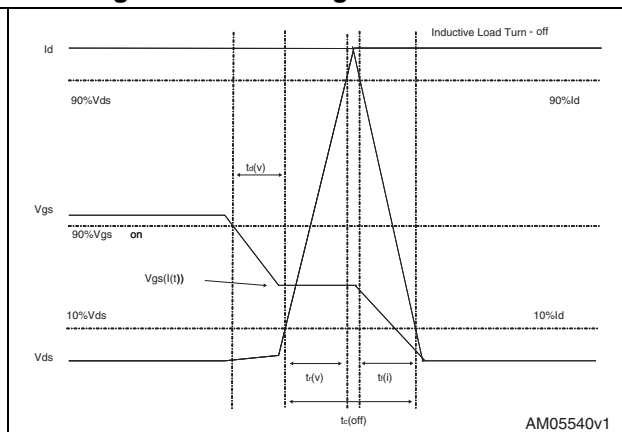


Figure 18. Switching time waveform





## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Figure 19. DPAK (TO-252) type A drawing

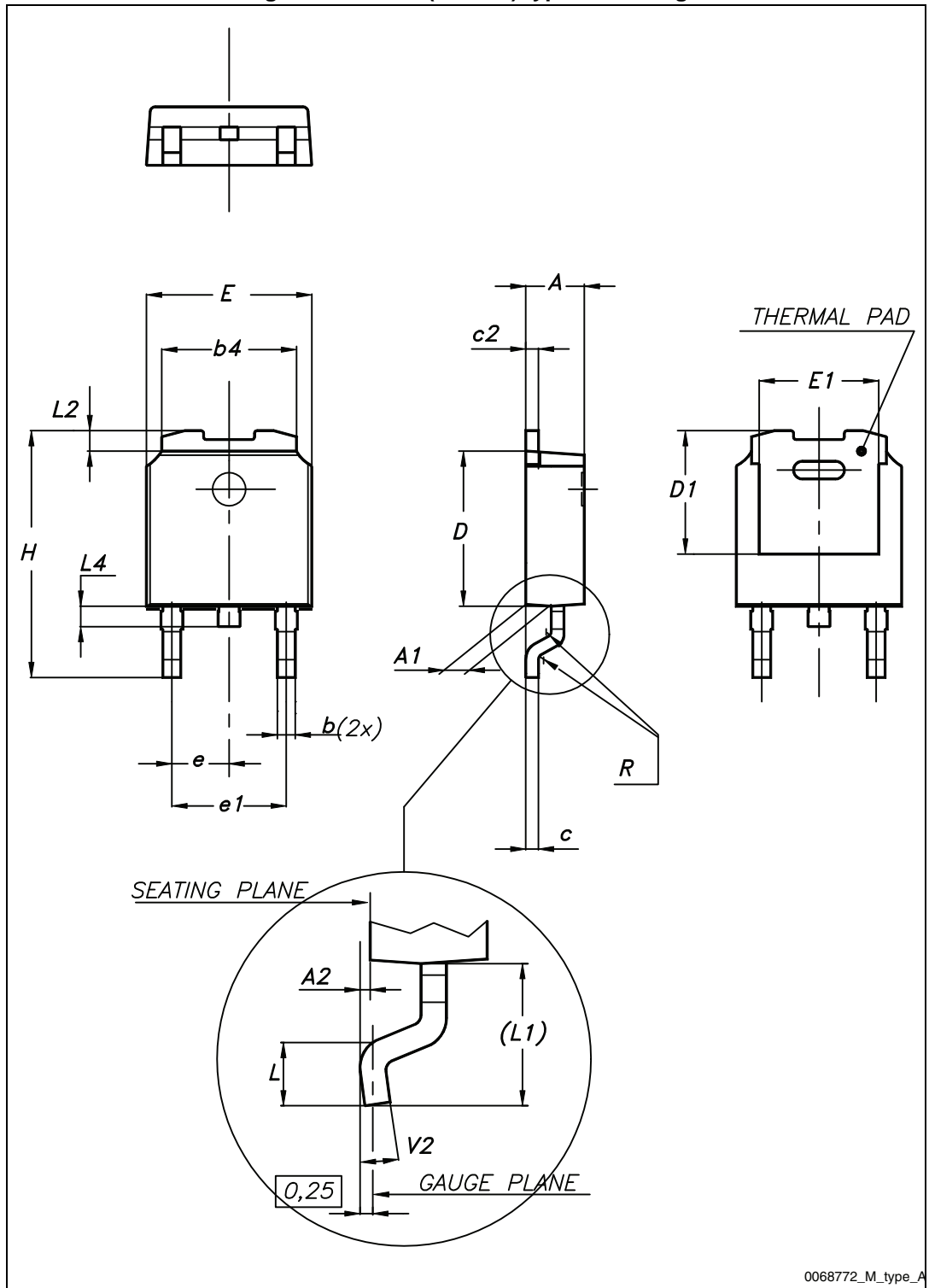
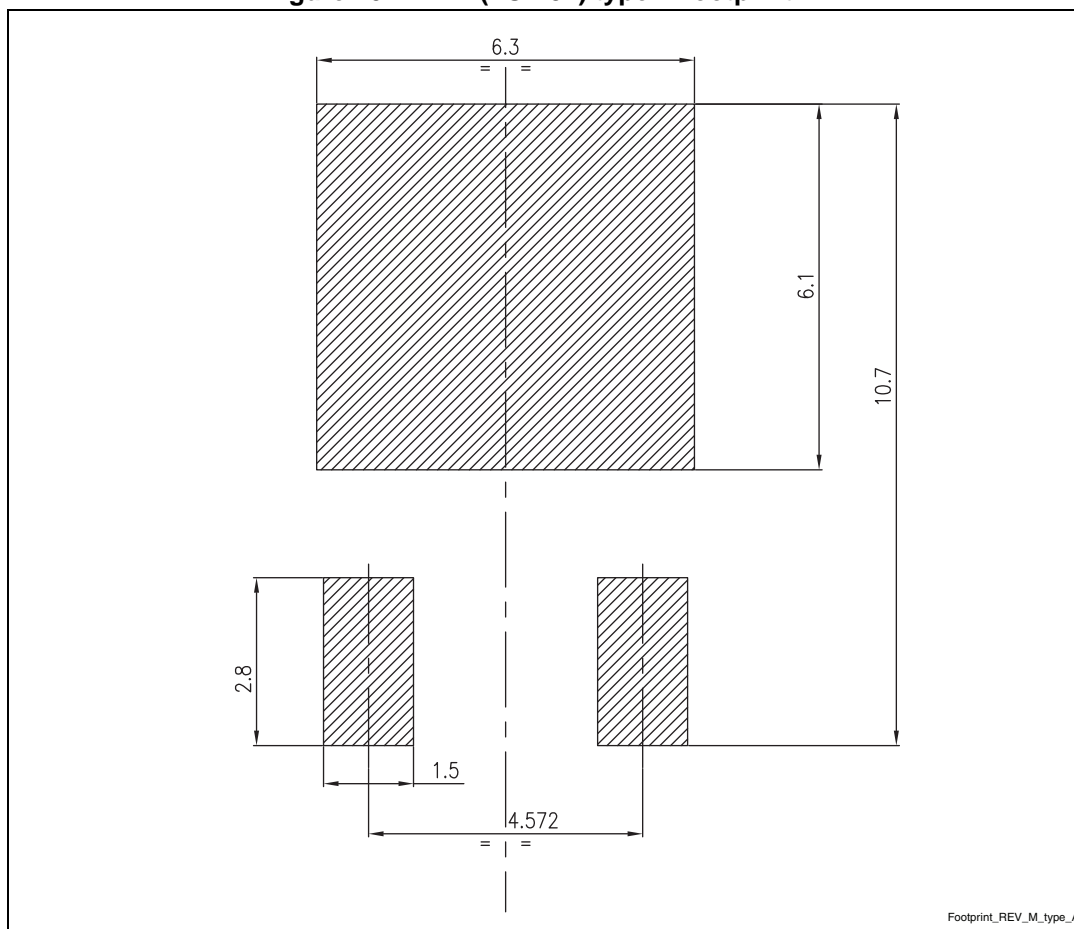


Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20. DPAK (TO-252) type A footprint (a)



a. All dimensions are in millimeters

# 5 Packaging mechanical data

Figure 21. Tape for DPAK (TO-252)

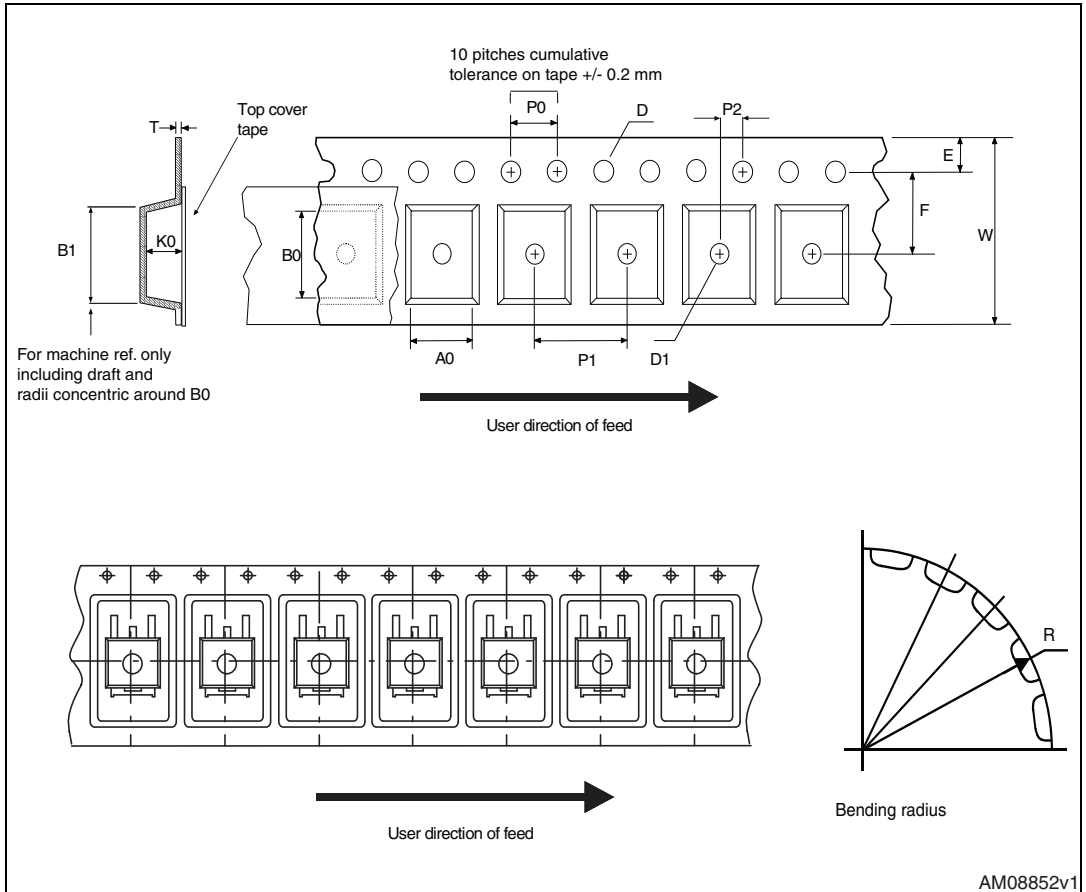


Figure 22. Reel for DPAK (TO-252)

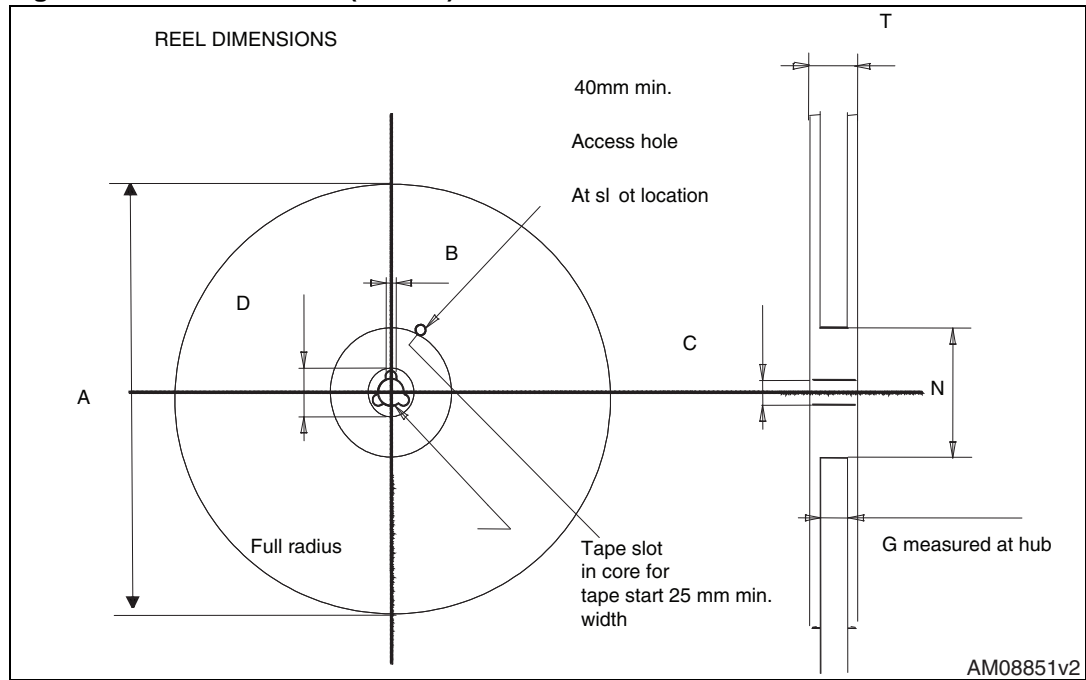


Table 9. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

## 6 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
03-Mar-2014	1	Initial release. The part number previously included in datasheet DocID023839

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